

SANYO

No.1943A

2SA1392/2SC3383

PNP/NPN Epitaxial Planar Silicon Transistors

AF Amp Applications

Features

- Adoption of FBET process
- AF amp

(): 2SA1392

Absolute Maximum Ratings at $T_a=25^{\circ}\text{C}$

			unit
Collector to Base Voltage	V_{CB0}	(-)60	V
Collector to Emitter Voltage	V_{CE0}	(-)50	V
Emitter to Base Voltage	V_{EB0}	(-)6	V
Collector Current	I_C	(-)200	mA
Collector Current (Pulse)	I_{CP}	(-)400	mA
Collector Dissipation	P_C	400	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics at $T_a=25^{\circ}\text{C}$

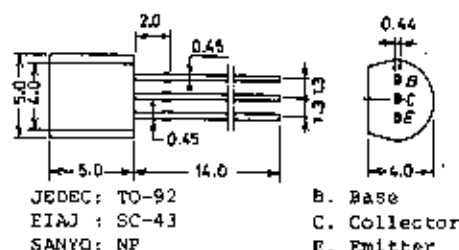
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40\text{V}, I_E=0$		(-)0.1		μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)5\text{V}, I_C=0$		(-)0.1		μA
DC Current Gain	$h_{FE}(1)$	$V_{CE}=(-)6\text{V}, I_C=(-)1\text{mA}$	100*		560*	
	$h_{FE}(2)$	$V_{CE}=(-)6\text{V}, I_C=(-)0.1\text{mA}$	70			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)6\text{V}, I_C=(-)10\text{mA}$		250		MHz
				(200)		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)100\text{mA}, I_E=(-)10\text{mA}$		(-)0.3		V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)100\text{mA}, I_E=(-)10\text{mA}$		(-)1.0		V
Output Capacitance	C_{ob}	$V_{CB}=(-)6\text{V}, f=1\text{MHz}$		2.7		pF
				(3.7)		pF
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-)60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-)50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}, I_C=0$	(-)6			V

*: The 2SA1392/2SC3383 are classified by 1mA h_{FE} as follows:

100	R	200	140	S	280	200	T	400	280	U	560
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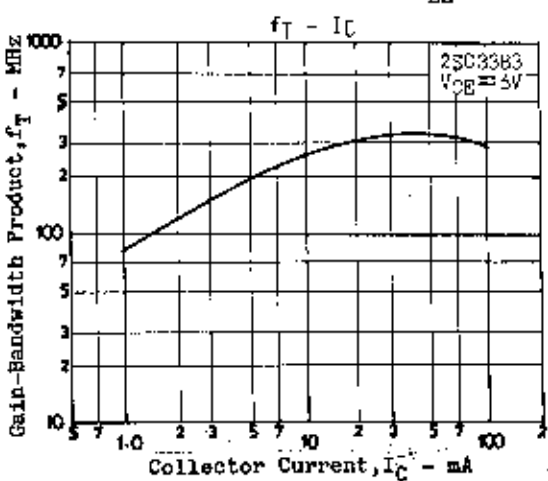
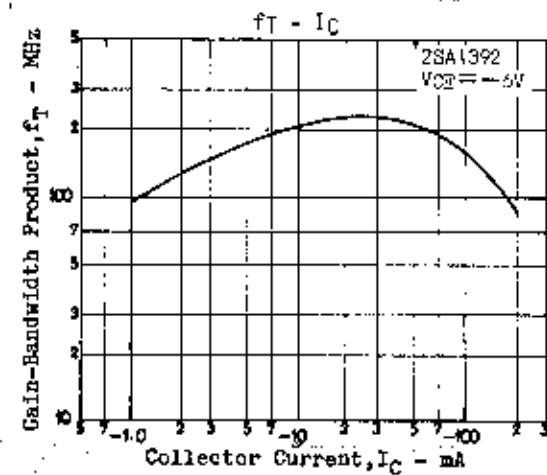
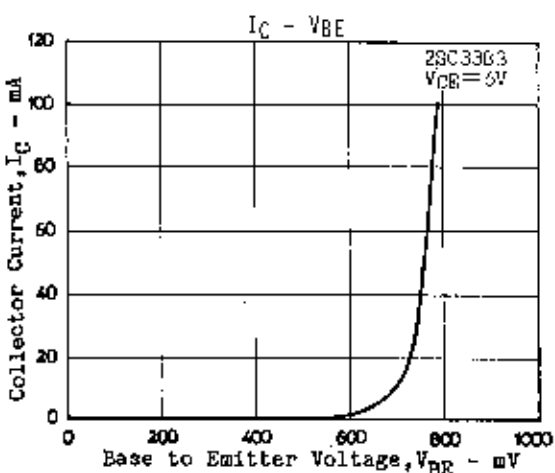
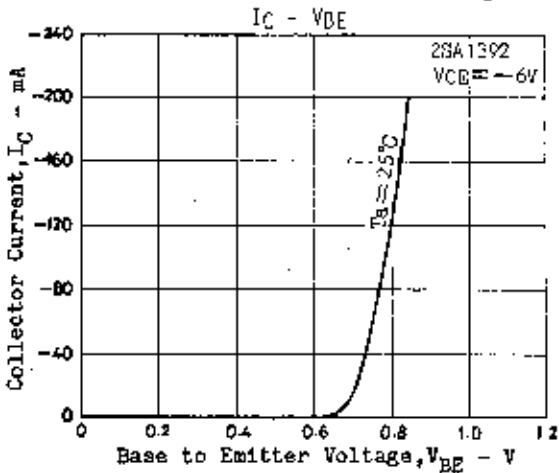
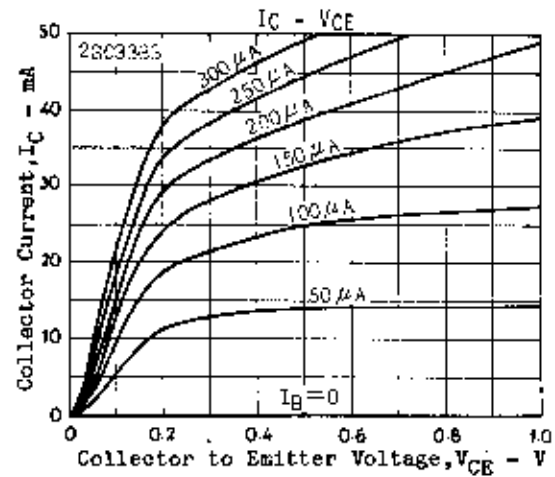
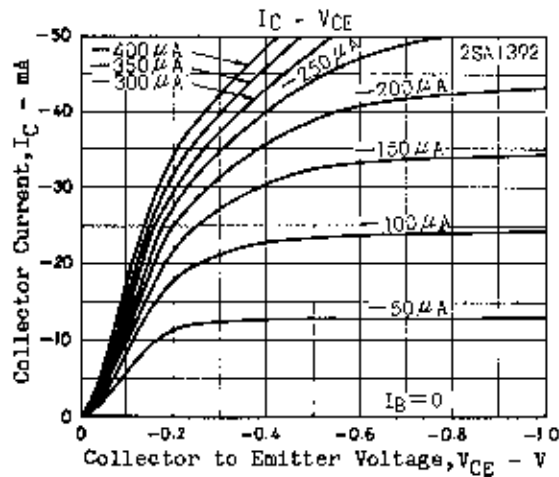
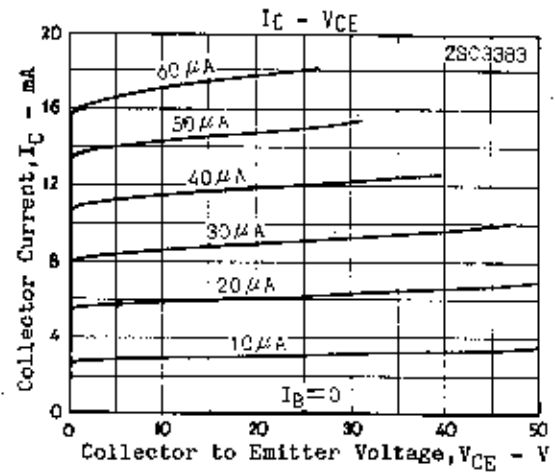
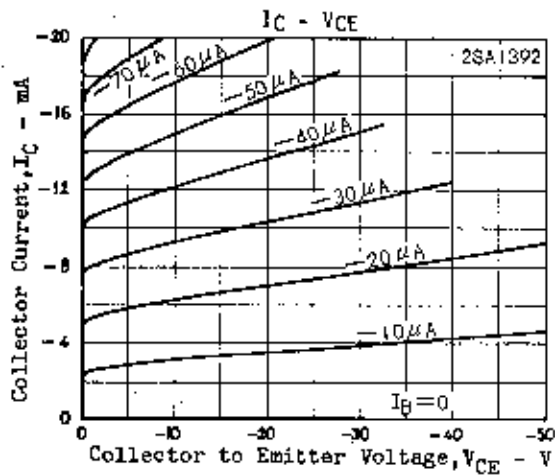
Package Dimensions 2003A

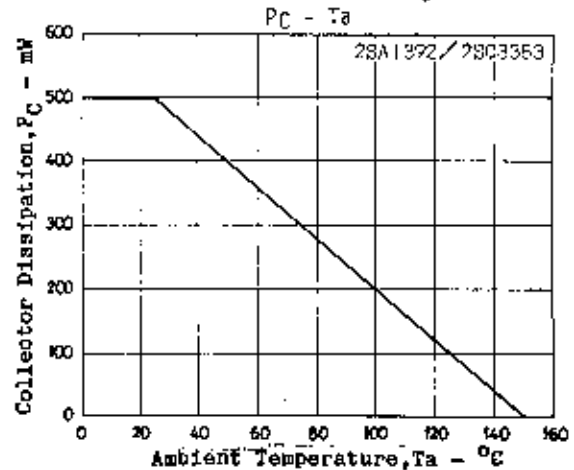
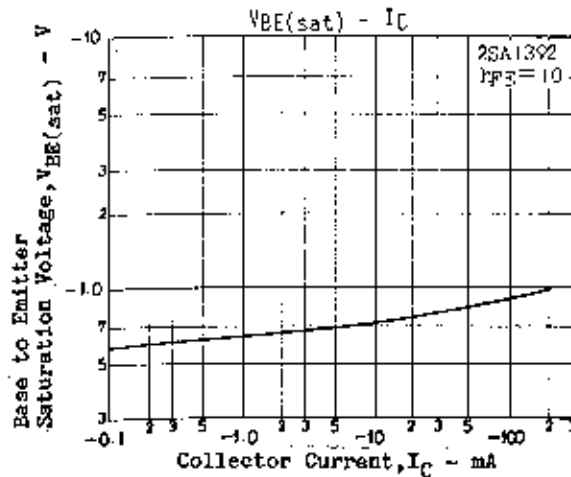
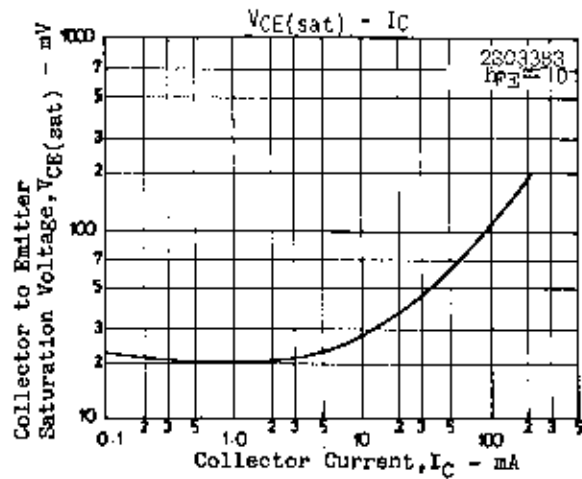
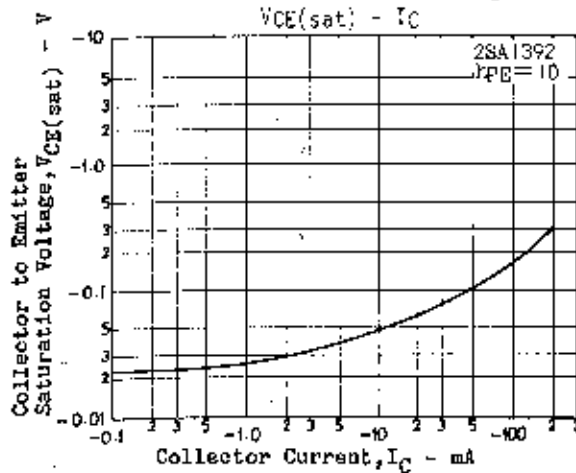
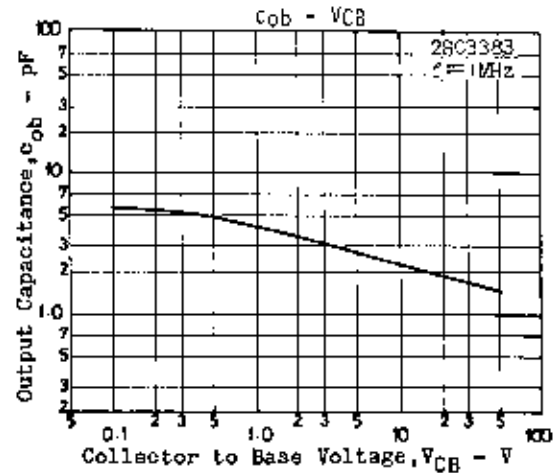
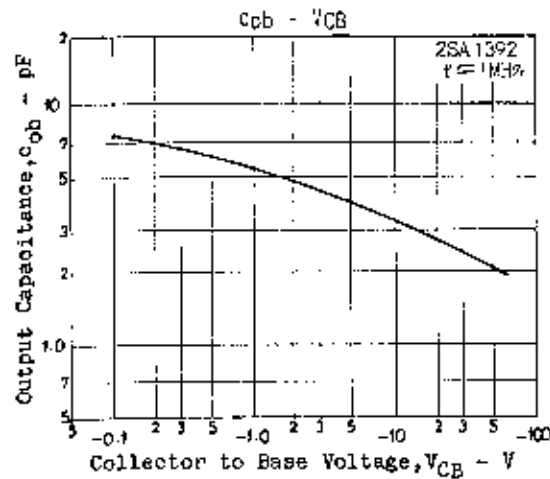
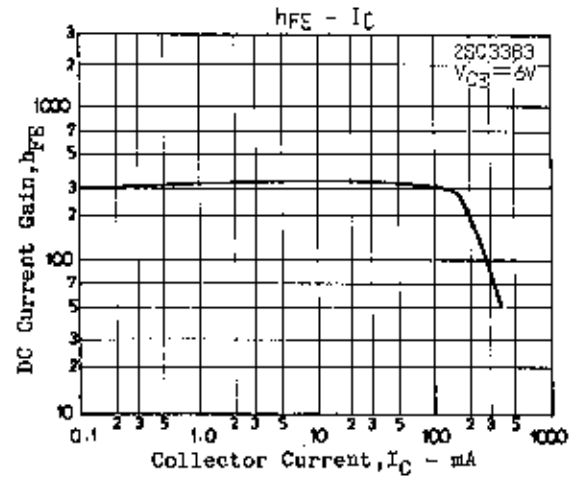
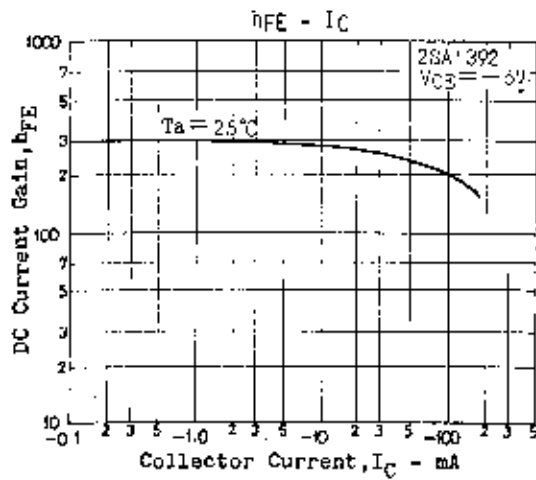
(unit: mm)

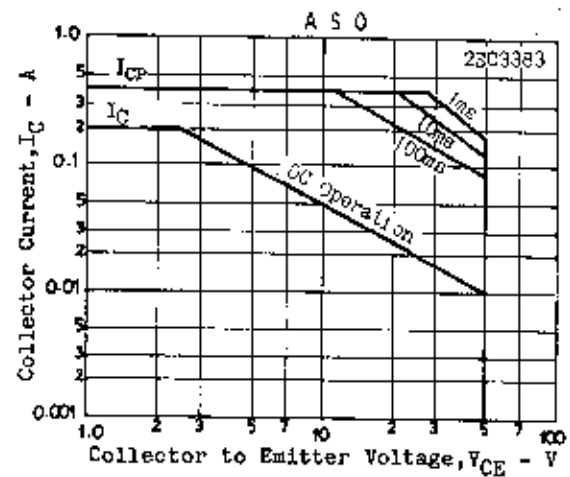
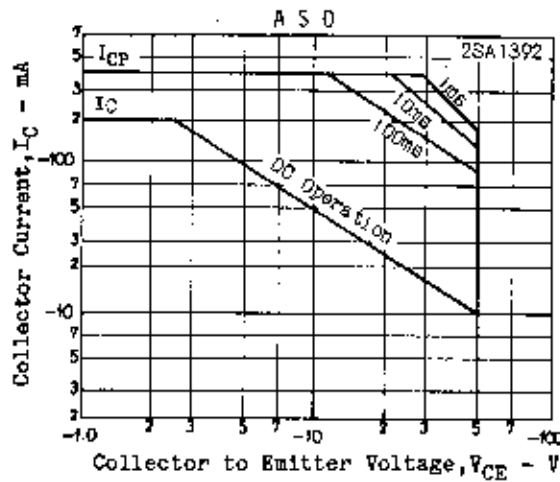


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